so as to be substantially in parallel with each other, and

an actual wiring length l of said signal line being longer than a wiring length l_0 determined by the following equation

$$l_0 = \sqrt{\frac{\frac{L}{C} + \sqrt{\frac{R^2 + 8\pi^2 f_0^2 L^2}{4\pi^2 f_0^2 C^2}}}{R^2 + 4\pi^2 f_0^2 L^2}}$$

where R represents a resistance component, L represents an inductance component, and C represent a capacitance component per unit length of said signal line in such a case that said differential signal line does not exist.

4. (Amended) The semiconductor device according to claim 1, wherein there are at least two of said signal lines, which are formed in the same layer, and a second differential signal line different from said first differential signal line is formed between said at least two signal lines in the same layer.

Please add new Claims 13-18 as follows:

--13. (New) The semiconductor device according to claim 1, wherein the frequency f_0 is 1GHz or more.

14. (New) A semiconductor device comprising:

at least two signal lines, each being capable of passing a first signal, formed in the same layer above a semiconductor substrate,

first differential signal lines through which a signal in opposite phase to said first signal passes, or which is connected to a ground power supply; and

said signal lines and said first differential signal lines being laminated via an insulating